

**Method for Transistor Gate Dielectric Layer with Uniform
Nitrogen Concentration**

5 ABSTRACT OF THE INVENTION

The instant invention describes a method for forming a dielectric film with a uniform concentration of nitrogen. The films are formed by first incorporating nitrogen into a dielectric film using RPNO. The films are then annealed in
10 N₂O which redistributes the incorporated species to produce a uniform nitrogen concentration.

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F08260-44029660